



PATENT
Attorney Docket No. 210013

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Tadatomo et al.

Application No. 09/787,502

Art Unit: 2815

Examiner: E. Ortiz

Filed: March 16, 2001

For: SEMICONDUCTOR LIGHT
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RESPONSE TO OFFICE ACTION

Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Office Action dated July 3, 2002, please enter the following amendments and consider the following remarks.

AMENDMENTS

IN THE CLAIMS:

Please amend claims 2, 6, and 8 to read as follows:

2. (Twice Amended) A semiconductor light receiving element comprising a light receiving layer comprising a GaN group semiconductor and an electrode formed on one surface of the light receiving layer as a light receiving surface in such a manner that the light can enter the light receiving layer, wherein the light receiving element is a Schottky barrier type light receiving element in which light enters a depletion layer formed under the electrode, which extends to cover a small area around the electrode from the side the electrode is formed, said light receiving layer is a first conductivity type layer, said electrode formed on said light receiving surface comprises at least a Schottky electrode, and a total of boundary lines between areas of the light receiving surface covered with the Schottky electrode and exposed areas is longer than the length of the outer periphery of the light receiving surface.

6. (Amended) The light receiving element of claim 2, wherein the light receiving layer is an uppermost layer of a laminate comprising one or more layers comprising a first